

Features

- Isolation: 48 dB Typical at 1 GHz
- High Intercept Point Over Wide Bandwidth
- Trise, Tfall: 5 nS Typical
- DIP Package
- Integral TTL Driver (CMOS Compatible)
- 50 Ohm Nominal Impedance

Description

M/A-COM's SW-137 is a GaAs MMIC SPDT reflective switch with an integral Silicon ASIC driver. This device is in a 14-lead DIP package. These switches offer high intercept points over a wide bandwidth of operation, while maintaining low DC power dissipation. These switches exhibit excellent performance and repeatability from 0.01 to 3.0 GHz. The SW-137 is ideally suited for RF/IF communications applications. Contact the factory for environmental screening.

Ordering Information

Part Number	Package
SW-137-PIN	DI-1

Note: Reference Application Note M513 for reel size information.

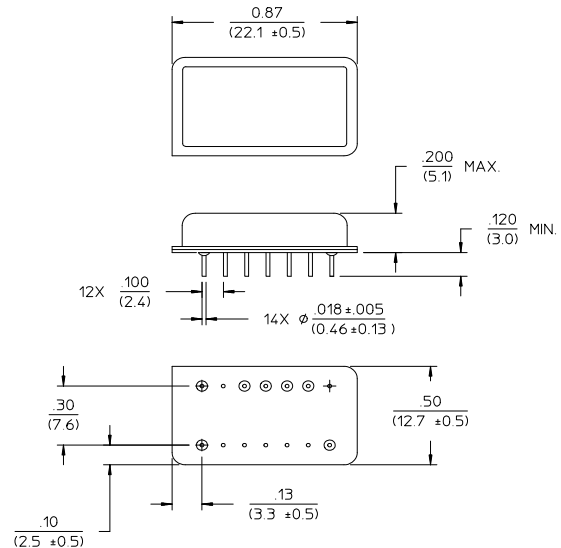
Note: Die quantity varies.

Absolute Maximum Ratings ²

Parameter	Absolute Maximum
Max Input Power 0.05 GHz 0.5 - 3.0 GHz	+27 dBm +34 dBm
Supply Voltages V _{cc} V _{ee}	-0.5V to +16.5 V -16.5V to +0.5V
Control Voltage	-0.5V to V _{cc} to +0.5V
Operating Temperature	-55°C to +125°C
Storage Temperature	-65°C to +150°C

2. Operation of this device above any one of these parameters may cause permanent damage.

Functional Block Diagram



Dimensions in () are in mm
Unless Otherwise Noted: .XXX = +0.010 (XX = +0.25)
.XX = ±0.02 (X = +0.5)
WEIGHT (APPROX): 0.14 OUNCES 4 GRAMS

Truth Table

Control Inputs	Condition of Switch RF Common to each RF Port	
	RF1	RF2
C1		
Low	On	Off
High	Off	On

Current (mA)

	± 9V	± 12V	± 15V
V _{cc}	8	11	15
V _{ee}	4	7	9

* Restrictions on Hazardous Substances, European Union Directive 2002/95/EC.

Electrical Specifications: $T_A = -55^{\circ}\text{C}$ to $+85^{\circ}\text{C}$ ¹

Parameter	Test Conditions	Frequency	Units	Min	Typ	Max
Reference Insertion Loss	—	0.01 - 0.5 GHz	dB	—	—	0.9
		0.01 - 1.0 GHz	dB	—	—	1.0
		0.01 - 2.0 GHz	dB	—	—	1.4
		0.01 - 3.0 GHz	dB	—	—	1.6
Isolation	—	0.01 - 0.5 GHz	dB	48	—	—
		0.01 - 1.0 GHz	dB	43	—	—
		0.01 - 2.0 GHz	dB	37	—	—
		0.01 - 3.0 GHz	dB	32	—	—
VSWR	—	0.01 - 0.5 GHz	Ratio	—	—	1.25:1
		0.01 - 1.0 GHz	Ratio	—	—	1.4:1
		0.01 - 2.0 GHz	Ratio	—	—	1.7:1
		0.01 - 3.0 GHz	Ratio	—	—	2.0:1
Trise, Tfall Ton, Toff Transients	10% to 90% 1.3V Control to 90/10% RF In-band (peak-peak)	—	nS	—	5	—
		—	nS	—	22	—
		—	mV	—	45	—
1 dB Compression		0.01 - 3.0 GHz	dBm	—	+25	—
Input IP_3	For two-tone Input power up to +5 dBm	0.01 - 3.0 GHz	dBm	—	+46	—
Input IP_2	For two-tone Input power up to +5 dBm	0.01 - 3.0 GHz	dBm	—	+76	—

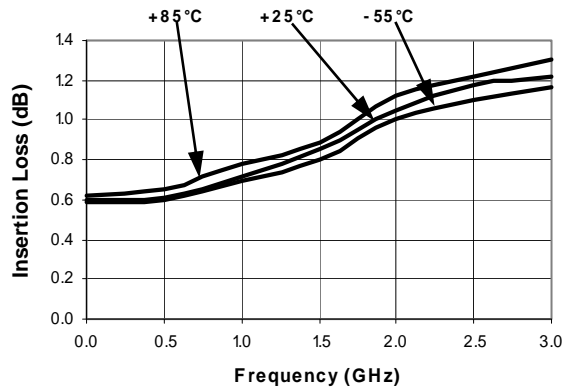
1. All specifications apply when operated with bias voltages of +9V to +15V for V_{cc} and -9 to -15V for V_{ee} and 50 Ohm impedance at all RF ports unless otherwise specified.

Electrical Specifications: $T_A = 25^{\circ}\text{C}$

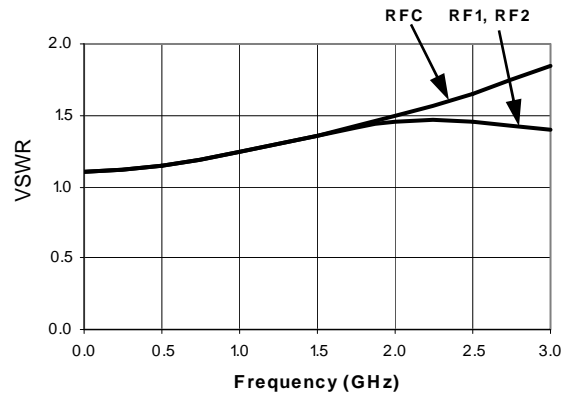
Parameter	Test Conditions	Frequency	Units	Min	Typ	Max
V_{cc} V_{ee}		— —	V V	+9 -15	+12 -12	+15 -9
I_{cc}	$V_{cc} = +9$ to $+15\text{V}$	—	mA	—	—	20.0
I_{ee}	$V_{ee} = -9$ to -15V	—	mA	—	—	15.0
V_{ctl} V_{ctl}	Low High	— —	V V	0.0 2.0	— —	0.8 5.0
Input Leakage Current (Low)	0 to 0.8V	—	μA	—	—	1.0
Input Leakage Current (High)	2.0 to 5.0V	—	μA	—	—	1.0

Typical Performance Curves

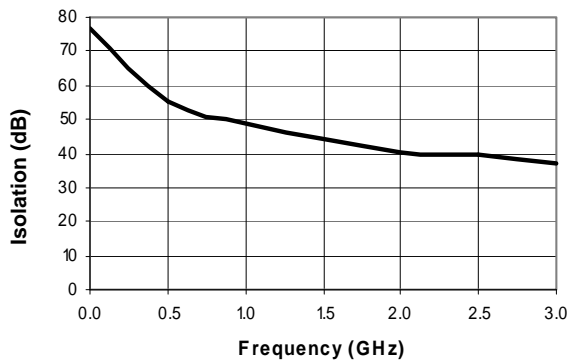
Insertion Loss vs. Frequency



VSWR vs. Frequency



Isolation vs. Frequency



Functional Schematic (Top View)

